

Abstract of the Disclosure:

An integrated, tunable capacitor has terminal regions that extend significantly deeper into the semiconductor body than the customary source/drain terminal regions in the

5 conventional CMOS varactors. For this purpose, by way of example, well-type regions or collector deep implantation regions may be provided, with which the depleted regions occurring in the event of large tuning voltages extend significantly further into the semiconductor body. The

10 varactor with a large tuning range can be produced without additional outlay in mass production methods and can be used, for example, in phase-locked loops.

15 MPW/nt